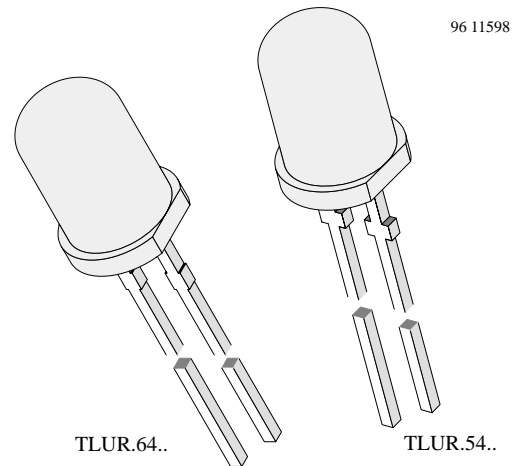


Universal LED in ø 5 mm Tinted Diffused Package

Color	Type	Technology	Angle of Half Intensity $\pm\varphi$
Red	TLUR54../TLUR64..	GaAsP on GaAs	30°

Features

- For DC and pulse operation
- Luminous intensity categorized
- Standard ø 5 mm (T-1 $\frac{3}{4}$) package
- TLUR54.. with stand-offs
- TLUR64.. without stand-offs



Applications

General indicating and lighting purposes

Absolute Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

TLUR54../TLUR64..

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	6	V
DC forward current		I_F	50	mA
Surge forward current	$t_p \leq 10 \mu\text{s}$	I_{FSM}	1	A
Power dissipation	$T_{amb} \leq 65^{\circ}\text{C}$	P_V	100	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55 to +100	$^{\circ}\text{C}$
Soldering temperature	$t \leq 5 \text{ s}$, 2 mm from body	T_{sd}	260	$^{\circ}\text{C}$
Thermal resistance junction/ambient		R_{thJA}	350	K/W

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Red (TLUR54../TLUR64..)

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Luminous intensity	$I_F = 10\text{ mA}$, $I_{Vmin}/I_{Vmax} \geq 0.5$	TLUR5400/6400	I_V	0.4	0.8		mcd
		TLUR5401/6401	I_V	1	2.5	5	mcd
Dominant wavelength	$I_F = 10\text{ mA}$		λ_d		645		nm
Peak wavelength	$I_F = 10\text{ mA}$		λ_p		660		nm
Angle of half intensity	$I_F = 10\text{ mA}$		ϕ		± 30		deg
Forward voltage	$I_F = 20\text{ mA}$		V_F		1.6	2	V
Reverse voltage	$I_R = 10\ \mu\text{A}$		V_R	6	15		V
Junction capacitance	$V_R = 0, f = 1\text{ MHz}$		C_j		50		pF

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

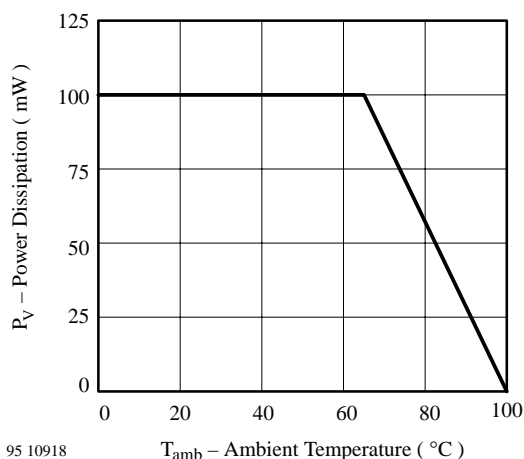


Figure 1 Power Dissipation vs. Ambient Temperature

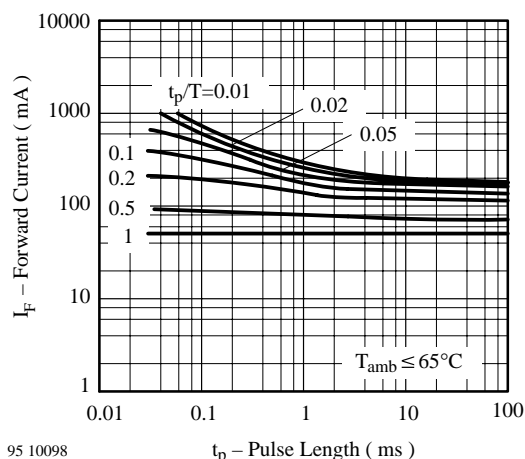


Figure 3 Forward Current vs. Pulse Length

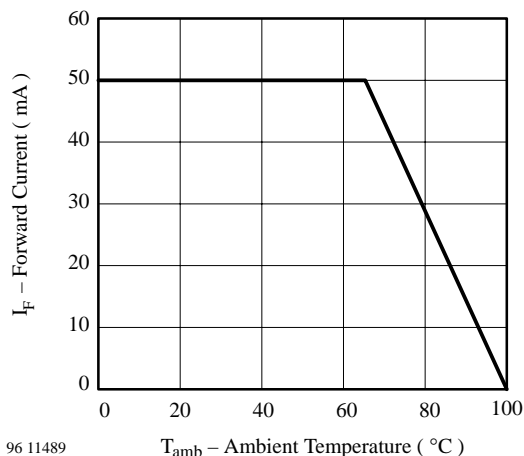


Figure 2 Forward Current vs. Ambient Temperature

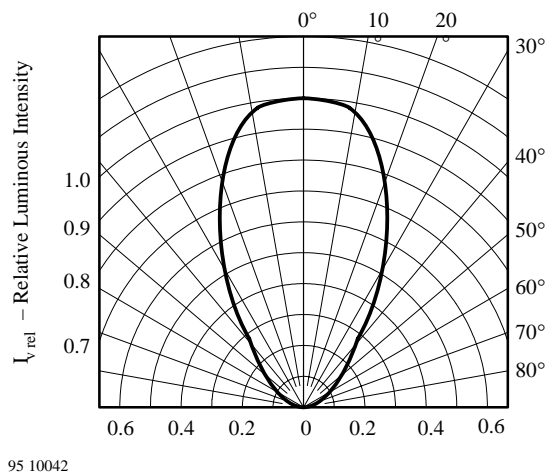


Figure 4 Rel. Luminous Intensity vs. Angular Displacement

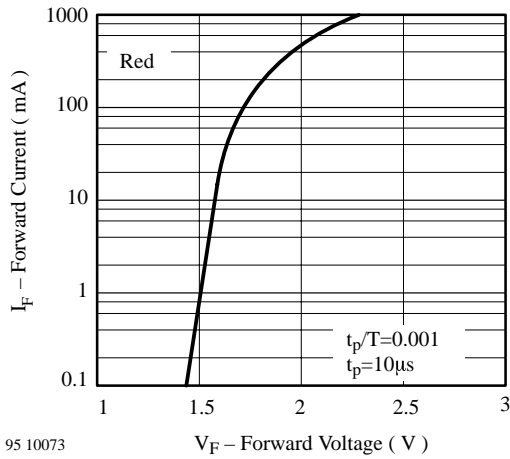


Figure 5 Forward Current vs. Forward Voltage

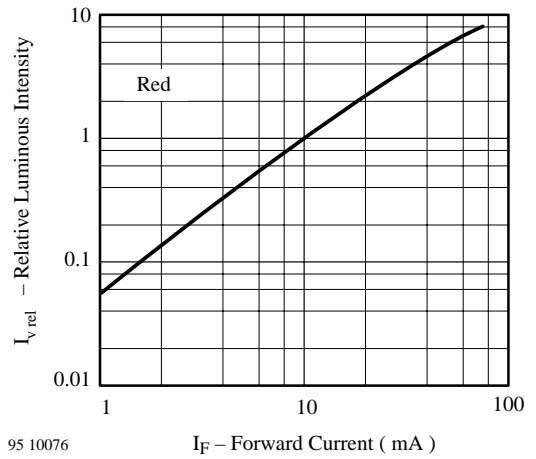


Figure 8 Relative Luminous Intensity vs. Forward Current

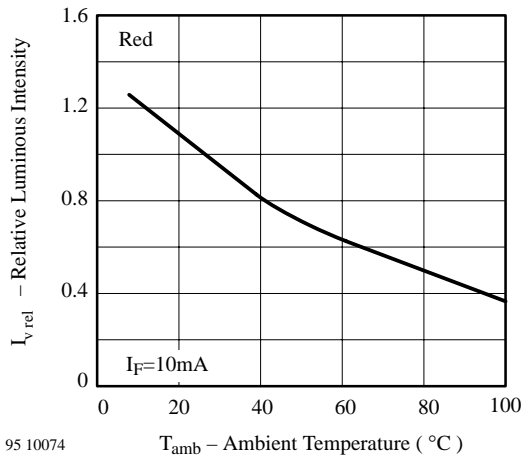


Figure 6 Rel. Luminous Intensity vs. Ambient Temperature

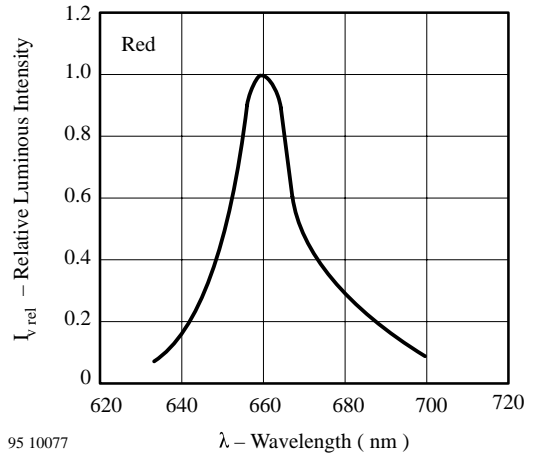


Figure 9 Relative Luminous Intensity vs. Wavelength

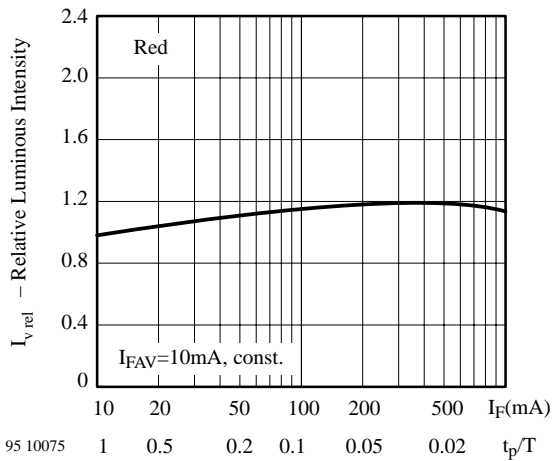
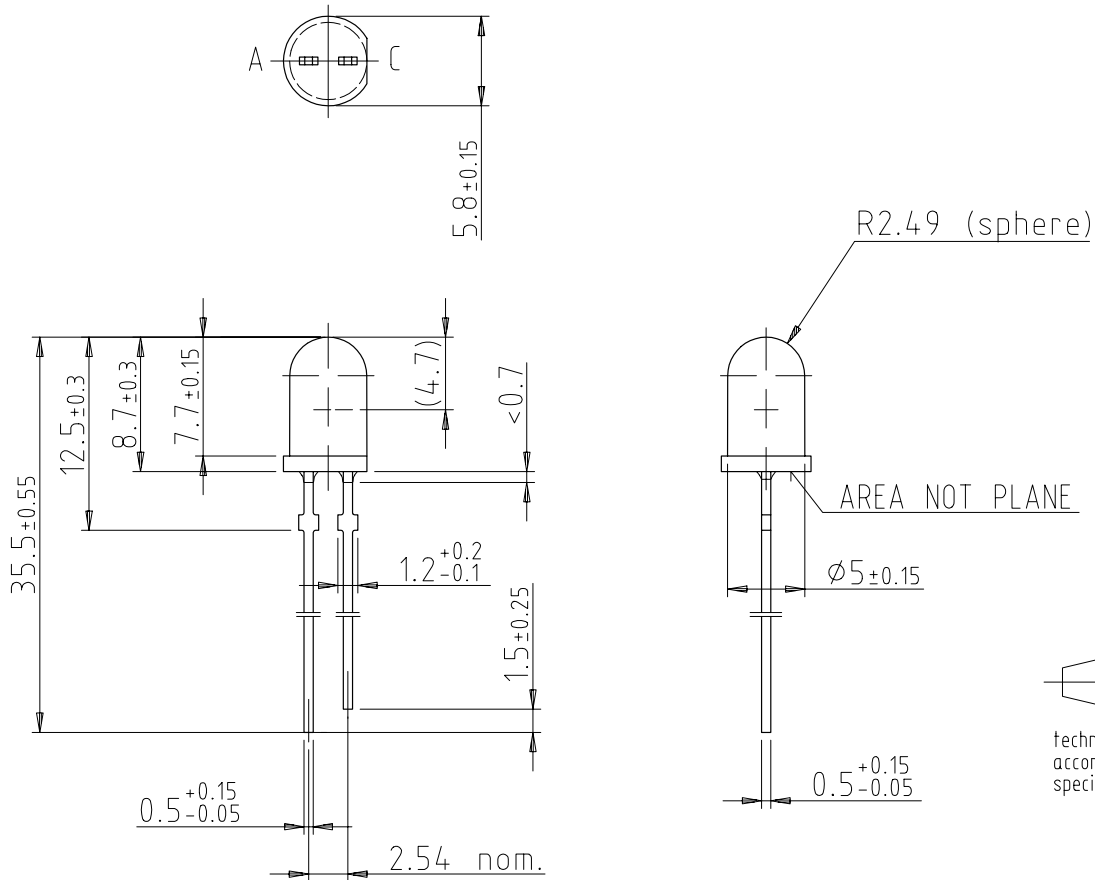
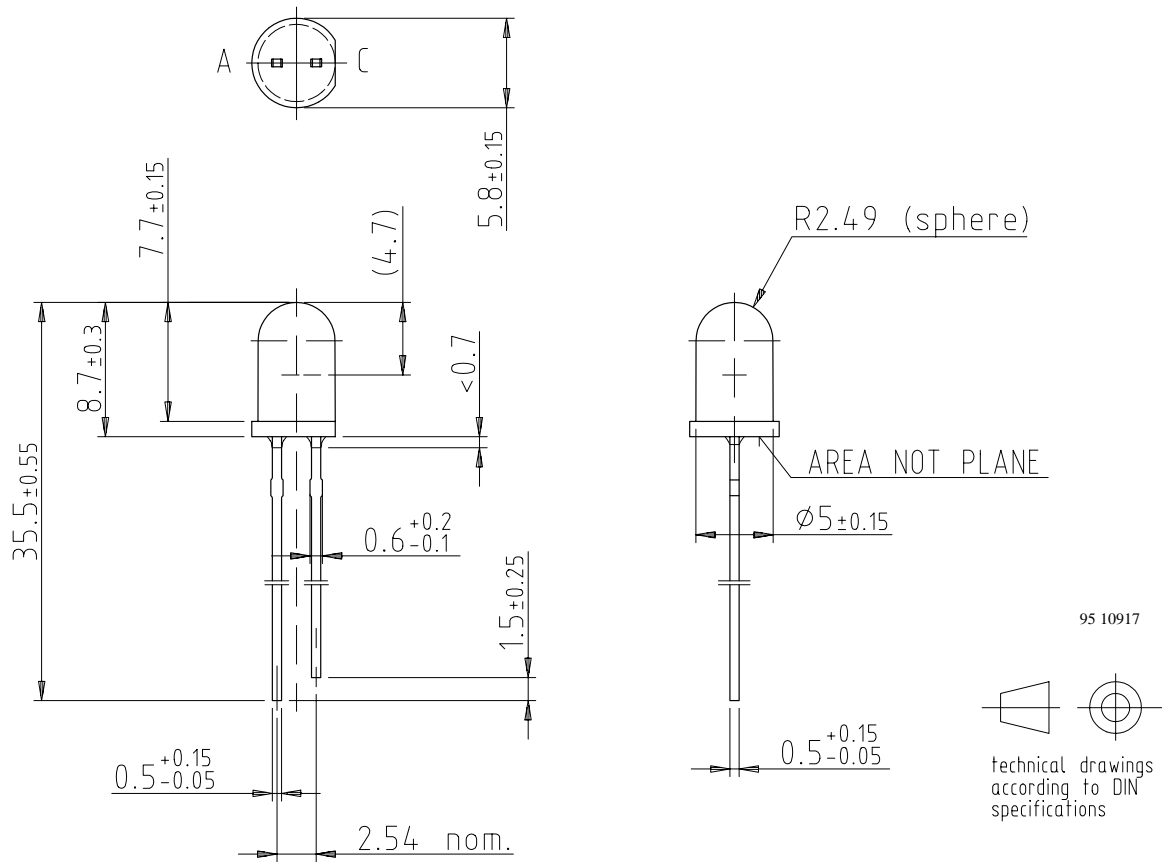


Figure 7 Rel. Lumin. Intensity vs.
 Forw. Current/Duty Cycle

Dimensions in mm



PCB Layout in mm



technical drawings according to DIN specifications



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0) 7131 67 2831, Fax number: 49 (0) 7131 67 2423

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9